

Shijie Xu

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

287
papers

7,480
citations

41
h-index

78
g-index

311
ext. papers

8,394
ext. citations

4
avg, IF

5.73
L-index

#	Paper	IF	Citations
287	Temperature-Dependent Electroluminescence of Phosphor-Converted White LEDs with K ₂ SiF ₆ :Mn ⁴⁺ below Room Temperature. <i>IEEE Electron Device Letters</i> , 2022 , 1-1	4.4	0
286	Multiple Optical Beam Switching for Physical Layer Security of Visible Light Communications. <i>IEEE Photonics Journal</i> , 2022 , 14, 1-9	1.8	1
285	High robust broadcasting over DTMB-A with low-rate LDPC codes. <i>China Communications</i> , 2022 , 19, 192-201	3.0	0
284	Luminescence performance and vibronic behavior of Mn-activated CaKAlZnO deep-red phosphor. <i>Optics Letters</i> , 2021 , 46, 5938-5941	3	0
283	Large negative thermal quenching of yellow luminescence in non-polar InGa _N /Ga _N quantum wells. <i>Journal of Applied Physics</i> , 2021 , 130, 205704	2.5	2
282	High power GaN-based blue superluminescent diodes with low spectral modulation. <i>AIP Advances</i> , 2021 , 11, 045202	1.5	0
281	Effect of Graded-Indium-Content Superlattice on the Optical and Structural Properties of Yellow-Emitting InGa _N /Ga _N Quantum Wells. <i>Materials</i> , 2021 , 14,	3.5	1
280	Selective Excitation of CdSe/CdS Dot-in-Rod Nanocrystals and Distinct Roles of Electrons and Holes in Photophysical and Photochemical Interactions with Ambient Air. <i>Physica Status Solidi (B): Basic Research</i> , 2021 , 258, 2100092	1.3	0
279	Gate Reliability and its Degradation Mechanism in the Normally OFF High-Electron-Mobility Transistors With Regrown p-GaN Gate. <i>IEEE Journal of Emerging and Selected Topics in Power Electronics</i> , 2021 , 9, 3715-3724	5.6	5
278	Carrier recombination dynamics in green InGa _N -LEDs with quantum-dot-like structures. <i>Journal of Materials Science</i> , 2021 , 56, 1481-1491	4.3	0
277	Stable, High-Efficiency Voltage-Dependent Color-Tunable Organic Light-Emitting Diodes with a Single Tetradentate Platinum(II) Emitter Having Long Operational Lifetime. <i>Advanced Materials</i> , 2021 , 33, e2004873	24	12
276	Variable-period oscillations in optical spectra in sub-bandgap long wavelength region: signatures of new dispersion of refractive index?. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 155102	3	3
275	Thermal behaviors of the sharp zero-phonon luminescence lines of NV center in diamond. <i>Journal of Luminescence</i> , 2021 , 236, 118081	3.8	0
274	Local laser heating effects in monolayer WS ₂ probed by photoluminescence. <i>Applied Surface Science</i> , 2021 , 562, 150226	6.7	0
273	Effect of Si Doping on the Performance of GaN Schottky Barrier Ultraviolet Photodetector Grown on Si Substrate. <i>Photonics</i> , 2021 , 8, 28	2.2	2
272	Nitrogen-Implanted Guard Rings for 600-V Quasi-Vertical GaN-on-Si Schottky Barrier Diodes With a BFOM of 0.26 GW/cm ² . <i>IEEE Transactions on Electron Devices</i> , 2021 , 1-5	2.9	7
271	GaN-Based Resonant-Cavity Light-Emitting Diodes Grown on Si.. <i>Nanomaterials</i> , 2021 , 12,	5.4	1

270	Luminescence Characteristics and Vibronic Coupling Behavior of a Highly Efficient Eu ²⁺ -Activated RbLi ₇ Si ₂ O ₈ Green Phosphor for Wide Color Gamut WLEDs. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 3749-3755	4	3
269	Large-scale quantification of aluminum in Al _x Ga _{1-x} N alloys by ToF-SIMS: The benefit of secondary cluster ions. <i>Surface and Interface Analysis</i> , 2020 , 52, 311-317	1.5	2
268	Interdigital Structure Enhanced the Current Spreading and Light Output Power of GaN-Based Light Emitting Diodes. <i>IEEE Access</i> , 2020 , 8, 105972-105979	3.5	1
267	Direct Observation of One-Dimensional Peierls-type Charge Density Wave in Twin Boundaries of Monolayer MoTe. <i>ACS Nano</i> , 2020 , 14, 8299-8306	16.7	4
266	Radio-Optics Hybrid Single Frequency Network for DTTB: Principle, Technology, and Practice. <i>IEEE Transactions on Broadcasting</i> , 2020 , 66, 857-866	4.7	1
265	The key roles of 4f-level splitting and vibronic coupling in the high-efficiency luminescence of Ce ³⁺ ion in LuAG transparent ceramic phosphors. <i>Journal of Luminescence</i> , 2020 , 225, 117360	3.8	4
264	A p-GaN-Gated Hybrid Anode Lateral Diode with a Thicker AlGaN Barrier Layer. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020 , 217, 1900781	1.6	4
263	Photoluminescence signatures of thermal expansion, electron-phonon coupling and phase transitions in cesium lead bromide perovskite nanosheets. <i>Nanoscale</i> , 2020 , 12, 7315-7320	7.7	16
262	The strain, energy band and photoluminescence of GaAs _{0.92} Sb _{0.08} /Al _{0.3} Ga _{0.7} As multiple quantum wells grown on GaAs substrate. <i>Solid State Communications</i> , 2020 , 309, 113837	1.6	5
261	Determination of absorption coefficients and Urbach tail depth of ZnO below the bandgap with two-photon photoluminescence. <i>Optics Express</i> , 2020 , 28, 13817-13825	3.3	5
260	Steady-state and time-resolved upconversion photoluminescence in Yb-Er co-doped transparent ceramics of YAG. <i>Optics Letters</i> , 2020 , 45, 5712-5715	3	4
259	Impact of excitation energy on the excitonic luminescence of cesium lead bromide perovskite nanosheets. <i>Optics Letters</i> , 2020 , 45, 3881-3884	3	1
258	Determination of carbon-related trap energy level in (Al)GaN buffers for high electron mobility transistors through a room-temperature approach. <i>Applied Physics Letters</i> , 2020 , 117, 263501	3.4	10
257	InGaN-Based Lasers with an Inverted Ridge Waveguide Heterogeneously Integrated on Si(100). <i>ACS Photonics</i> , 2020 , 7, 2636-2642	6.3	2
256	Design and growth of GaN-based blue and green laser diodes. <i>Science China Materials</i> , 2020 , 63, 1348-1363	6.3	13
255	Local Phonon Modes Concerned with the Self-Trapped Exciton State in CsPbBr ₃ Nanocrystals. <i>Journal of Physical Chemistry C</i> , 2020 , 124, 27130-27135	3.8	5
254	Photoluminescence and Raman Scattering Signatures of Anisotropic Optical Properties in Freestanding m-, a- and c-Plane GaN Substrates. <i>Journal of Physical Chemistry C</i> , 2020 , 124, 18203-18208	3.8	2
253	The role of luminescence self-absorption in photocatalytic properties of self-assembled ZnS nanocrystals. <i>AIP Advances</i> , 2020 , 10, 105314	1.5	1

252	Self-terminated Gate Recessing with a Low Density of Interface States and High Uniformity for Enhancement-mode GaN HEMTs 2020 ,		1
251	High-performance UV detectors based on room-temperature deposited amorphous Ga ₂ O ₃ thin films by RF magnetron sputtering. <i>Journal of Materials Chemistry C</i> , 2019 , 7, 11834-11844	7.1	22
250	Dopant-Induced Electric Fields and Their Influence on the Band-Edge Absorption of GaN. <i>ACS Omega</i> , 2019 , 4, 15401-15406	3.9	1
249	Mechanism of Single-Photon Upconversion Photoluminescence in All-Inorganic Perovskite Nanocrystals: The Role of Self-Trapped Excitons. <i>Journal of Physical Chemistry Letters</i> , 2019 , 10, 5989-5996	6.4	21
248	Anomalous Temperature-Dependent Exciton-Phonon Coupling in Cesium Lead Bromide Perovskite Nanosheets. <i>Journal of Physical Chemistry C</i> , 2019 , 123, 5128-5135	3.8	30
247	Effective lifetimes of minority carriers in time-resolved photocurrent and photoluminescence of a doped semiconductor: Modelling of a GaInP solar cell. <i>Solar Energy Materials and Solar Cells</i> , 2019 , 193, 292-297	6.4	3
246	Luminescence landscapes of nitrogen-vacancy centers in diamond: quasi-localized vibrational resonances and selective coupling. <i>Journal of Materials Chemistry C</i> , 2019 , 7, 8086-8091	7.1	15
245	Behavior of Raman modes in InPbI alloys under hydrostatic pressure. <i>AIP Advances</i> , 2019 , 9, 035120	1.5	
244	Room-temperature continuous-wave operation of GaN-based blue-violet laser diodes with a lifetime longer than 1000 h. <i>Journal of Semiconductors</i> , 2019 , 40, 022801	2.3	24
243	Storage and transfer of optical excitation energy in GaInP epilayer: Photoluminescence signatures. <i>Journal of Materials Science and Technology</i> , 2019 , 35, 1364-1367	9.1	1
242	The roles of self-absorption and radiative energy transfer in photoluminescence of N-doped carbon nanodots in solution. <i>AIP Advances</i> , 2019 , 9, 035135	1.5	4
241	Key Technologies and Measurements for DTMB-A System. <i>IEEE Transactions on Broadcasting</i> , 2019 , 65, 53-64	4.7	14
240	InGaN-Based Quantum Well Superluminescent Diode Monolithically Grown on Si. <i>ACS Photonics</i> , 2019 , 6, 2104-2109	6.3	5
239	Field trial of UHDTV over Digital Television Terrestrial Broadcasting network 2019 ,		2
238	Results of the DTMB-A Field Trials in Hong Kong 2019 ,		1
237	Precise determination of surface band bending in Ga-polar n-GaN films by angular dependent X-Ray photoemission spectroscopy. <i>Scientific Reports</i> , 2019 , 9, 16969	4.9	10
236	Accurate surface band bending determination on Ga-polar n-type GaN films by fitting x-ray valence band photoemission spectrum. <i>AIP Advances</i> , 2019 , 9, 115106	1.5	6
235	Anomalous variable-temperature photoluminescence of CsPbBr perovskite quantum dots embedded into an organic solid. <i>Nanoscale</i> , 2019 , 11, 20942-20948	7.7	6

234	Broadband Spin-Driven Anomalous Surface Plasmon Polariton Steering via V-Shaped Aperture Metasurfaces. <i>Advanced Theory and Simulations</i> , 2019 , 2, 1800167	3.5	18
233	Theoretical Design of Plasmonic Refractive Index Sensor Based on the Fixed Band Detection. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2019 , 25, 1-6	3.8	6
232	Sub-Wavelength Grating Enhanced Ultra-Narrow Graphene Perfect Absorber. <i>Plasmonics</i> , 2018 , 13, 2267-2272	2.7	14
231	Room-Temperature Electrically Injected AlGaIn-Based near-Ultraviolet Laser Grown on Si. <i>ACS Photonics</i> , 2018 , 5, 699-704	6.3	31
230	Engineering the Exciton Dissociation in Quantum-Confined 2D CsPbBr ₃ Nanosheet Films. <i>Advanced Functional Materials</i> , 2018 , 28, 1705908	15.6	77
229	Luminescence and thermal behaviors of free and trapped excitons in cesium lead halide perovskite nanosheets. <i>Nanoscale</i> , 2018 , 10, 9949-9956	7.7	80
228	Effective Photon Recycling and Super Long Lived Minority Carriers in GaInP/GaAs Heterostructure Solar Cell: A Time-Resolved Optical Study. <i>IEEE Journal of Photovoltaics</i> , 2018 , 8, 820-824	3.7	7
227	Dynamic Control of Double Plasmon-Induced Transparencies in Aperture-Coupled Waveguide-Cavity System. <i>Plasmonics</i> , 2018 , 13, 345-352	2.4	74
226	Dark Mode Driven Extra-narrow and Multiband Absorber. <i>Plasmonics</i> , 2018 , 13, 729-735	2.4	8
225	Understanding and manipulating luminescence in carbon nanodots. <i>Carbon</i> , 2018 , 126, 58-64	10.4	24
224	Room-temperature continuous-wave electrically pumped InGaIn/GaN quantum well blue laser diode directly grown on Si. <i>Light: Science and Applications</i> , 2018 , 7, 13	16.7	73
223	Observation of two-times self-focusing of femtosecond laser beam in ZnO crystal by two-photon luminescence. <i>Science Bulletin</i> , 2018 , 63, 1392-1396	10.6	4
222	Large Negative-Thermal-Quenching Effect in Phonon-Induced Light Emissions in Mn-Activated Fluoride Phosphor for Warm-White Light-Emitting Diodes. <i>ACS Omega</i> , 2018 , 3, 13704-13710	3.9	24
221	On-wafer fabrication of cavity mirrors for InGaIn-based laser diode grown on Si. <i>Scientific Reports</i> , 2018 , 8, 7922	4.9	28
220	Ion Sputter Induced Interfacial Reaction in Prototypical Metal-GaN System. <i>Scientific Reports</i> , 2018 , 8, 8521	4.9	4
219	Quantum dot vertical-cavity surface-emitting lasers covering the 'green gap'. <i>Light: Science and Applications</i> , 2017 , 6, e16199	16.7	70
218	Excitation Dependent Phosphorous Property and New Model of the Structured Green Luminescence in ZnO. <i>Scientific Reports</i> , 2017 , 7, 41460	4.9	20
217	Electroluminescence probe of internal processes of carriers in GaInP single junction solar cell. <i>Solar Energy Materials and Solar Cells</i> , 2017 , 168, 201-206	6.4	7

216	A visible high efficiency and polarization-insensitive 34-level dielectric metasurface hologram. <i>RSC Advances</i> , 2017 , 7, 26371-26376	3.7	4
215	Abnormal gas pressure sensitivity of the visible emission in ZnO quantum dots prepared by improved sol-gel method: the role of surface polarity. <i>RSC Advances</i> , 2017 , 7, 29992-29997	3.7	3
214	Triplet harvesting in luminescent Cu(I) complexes by the thermally activated luminescence transition mechanism: impact of the molecular structure. <i>Journal of Materials Chemistry C</i> , 2017 , 5, 4488-4494	7.1	14
213	Performance Enhanced by Inserting an InGaN/GaN Shallower-Quantum Well Layer in InGaN Based Green Laser Diodes. <i>IEEE Photonics Journal</i> , 2017 , 9, 1-8	1.8	3
212	Integrated power line and visible light communication system compatible with multi-service transmission. <i>IET Communications</i> , 2017 , 11, 104-111	1.3	26
211	Extinction of the zero-phonon line and the first-order phonon sideband in excitonic luminescence of ZnO at room temperature: the self-absorption effect. <i>Science Bulletin</i> , 2017 , 62, 1525-1529	10.6	10
210	Boosting phonon-induced luminescence in red fluoride phosphors via composition-driven structural transformations. <i>Journal of Materials Chemistry C</i> , 2017 , 5, 12105-12111	7.1	11
209	Reflective metalens with sub-diffraction-limited and multifunctional focusing. <i>Scientific Reports</i> , 2017 , 7, 12632	4.9	15
208	NANOTEXTURING EFFECTS IN GAN/INGAN MULTI-QUANTUM-WELLS LED PLANAR STRUCTURES 2017 , 341-368		
207	Physical implications of activation energy derived from temperature dependent photoluminescence of InGaN-based materials. <i>Chinese Physics B</i> , 2017 , 26, 077101	1.2	5
206	Role of free electrons in phosphorescence in n-type wide bandgap semiconductors. <i>Physical Chemistry Chemical Physics</i> , 2017 , 19, 30332-30338	3.6	1
205	GaN-Based Blue Laser Diodes With 2.2 W of Light Output Power Under Continuous-Wave Operation. <i>IEEE Photonics Technology Letters</i> , 2017 , 29, 2203-2206	2.2	18
204	Significant increase of quantum efficiency of green InGaN quantum well by realizing step-flow growth. <i>Applied Physics Letters</i> , 2017 , 111, 112102	3.4	13
203	Managing Green Emission in Coupled InGaN QW/Ds Nanostructures via Nanoengineering. <i>Journal of Physical Chemistry C</i> , 2017 , 121, 22523-22530	3.8	2
202	Tunable and high-sensitivity sensing based on Fano resonance with coupled plasmonic cavities. <i>Scientific Reports</i> , 2017 , 7, 10639	4.9	53
201	p-GaN Gate Enhancement-Mode HEMT Through a High Tolerance Self-Terminated Etching Process. <i>IEEE Journal of the Electron Devices Society</i> , 2017 , 5, 340-346	2.3	28
200	A real-time high-speed visible light communication system based on RGB-LEDs 2017 ,		9
199	Luminescence Anisotropy and Thermal Effect of Magnetic and Electric Dipole Transitions of Cr Ions in Yb:YAG Transparent Ceramic. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 43790-43798	9.5	11

198	Electron irradiation study of room-temperature wafer-bonded four-junction solar cell grown by MBE. <i>Solar Energy Materials and Solar Cells</i> , 2017 , 171, 118-122	6.4	12
197	A generalized model for time-resolved luminescence of localized carriers and applications: Dispersive thermodynamics of localized carriers. <i>Scientific Reports</i> , 2017 , 7, 13	4.9	62
196	Electrochemical half-reaction-assisted sub-bandgap photon sensing in a graphene hybrid photodetector. <i>NPG Asia Materials</i> , 2017 , 9, e436-e436	10.3	5
195	Fabrication of pH-responsive PLGA(UCNPs/DOX) nanocapsules with upconversion luminescence for drug delivery. <i>Scientific Reports</i> , 2017 , 7, 18014	4.9	47
194	Internal Luminescence Mechanisms of III-Nitride LEDs. <i>Series in Optics and Optoelectronics</i> , 2017 , 651-676		
193	Hydrothermal synthesis and luminescent properties of BaTiF ₆ :Mn ⁴⁺ red phosphor for LED backlighting. <i>Materials Research Bulletin</i> , 2016 , 73, 14-20	5.1	37
192	Room-temperature continuous-wave electrically injected InGaN-based laser directly grown on Si. <i>Nature Photonics</i> , 2016 , 10, 595-599	33.9	151
191	A set of manganese ion activated fluoride phosphors (A ₂ BF ₆ :Mn ⁴⁺ , A = K, Na, B = Si, Ge, Ti): synthesis below 0 °C and efficient room-temperature photoluminescence. <i>Journal of Materials Chemistry C</i> , 2016 , 4, 9561-9568	7.1	57
190	Catastrophic Degradation of InGaN/GaN Blue Laser Diodes. <i>IEEE Transactions on Device and Materials Reliability</i> , 2016 , 16, 638-641	1.6	2
189	Carrier Localization Effects in InGaN/GaN Multiple-Quantum-Wells LED Nanowires: Luminescence Quantum Efficiency Improvement and "Negative" Thermal Activation Energy. <i>Scientific Reports</i> , 2016 , 6, 34545	4.9	27
188	Influence of lattice vibrations on luminescence and transfer of excitons in WS ₂ monolayer semiconductors. <i>Journal Physics D: Applied Physics</i> , 2016 , 49, 465101	3	3
187	Photovoltaic Response of InGaN/GaN Multi-quantum Well Solar Cells Enhanced by Reducing p-type GaN Resistivity. <i>IEEE Journal of Photovoltaics</i> , 2016 , 6, 454-459	3.7	1
186	Normally OFF GaN-on-Si MIS-HEMTs Fabricated With LPCVD-SiN _x Passivation and High-Temperature Gate Recess. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 614-619	2.9	60
185	Who make transparent ZnO colorful? Ion implantation and thermal annealing effects. <i>Superlattices and Microstructures</i> , 2016 , 99, 208-213	2.8	5
184	Photoinduced doping and photoluminescence signature in an exfoliated WS ₂ monolayer semiconductor. <i>RSC Advances</i> , 2016 , 6, 27677-27681	3.7	21
183	Transition of radiative recombination channels from delocalized states to localized states in a GaInP alloy with partial atomic ordering: a direct optical signature of Mott transition?. <i>Nanoscale</i> , 2016 , 8, 7113-8	7.7	14
182	Green laser diodes with low operation voltage obtained by suppressing carbon impurity in AlGaIn: Mg cladding layer. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016 , 13, 245-247		9
181	Influence of residual carbon impurities in i-GaN layer on the performance of GaN-based p-i-n photodetectors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016 , 34, 011204	1.3	3

180	Investigation of breakdown mechanism during field emission process of AlN thin film microscopic cold cathode. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016 , 34, 012201	1.3	1
179	Band-edge optical transitions in a nonpolar-plane GaN substrate: exciton-phonon coupling and temperature effects. <i>Semiconductor Science and Technology</i> , 2016 , 31, 095004	1.8	7
178	Reduction of Polarization Field Strength in Fully Strained c-Plane InGaN/(In)GaN Multiple Quantum Wells Grown by MOCVD. <i>Nanoscale Research Letters</i> , 2016 , 11, 519	5	13
177	A novel transmission model for plasmon-induced transparency in plasmonic waveguide system with a single resonator. <i>RSC Advances</i> , 2016 , 6, 51480-51484	3.7	9
176	Influence of temperature and reverse bias on photocurrent spectrum and supra-bandgap spectral response of monolithic GaInP/GaAs double-junction solar cell. <i>Frontiers of Optoelectronics</i> , 2016 , 9, 306-311	2.8	1
175	Influence of GaInP ordering on the performance of GaInP solar cells. <i>Journal of Semiconductors</i> , 2016 , 37, 073001	2.3	2
174	Raman scattering studies of dilute InP _{1-x} Bi _x alloys reveal unusually strong oscillator strength for Bi-induced modes. <i>Semiconductor Science and Technology</i> , 2015 , 30, 094003	1.8	14
173	Effects of sulfur introduction on the UV and the visible emission properties of ZnO. <i>Journal of the Korean Physical Society</i> , 2015 , 66, 672-677	0.6	0
172	Luminescence signature of free exciton dissociation and liberated electron transfer across the junction of graphene/GaN hybrid structure. <i>Scientific Reports</i> , 2015 , 5, 7687	4.9	16
171	An Indoor Broadband Broadcasting System Based on PLC and VLC. <i>IEEE Transactions on Broadcasting</i> , 2015 , 61, 299-308	4.7	70
170	Strong quantum confinement effect and reduced Fröhlich exciton-phonon coupling in ZnO quantum dots embedded inside a SiO ₂ matrix. <i>Nanoscale</i> , 2015 , 7, 17482-7	7.7	10
169	Novel InGaPBi single crystal grown by molecular beam epitaxy. <i>Applied Physics Express</i> , 2015 , 8, 041201	2.4	5
168	Structural dependences of localization and recombination of photogenerated carriers in the top GaInP Subcells of GaInP/GaAs double-junction tandem solar cells. <i>ACS Applied Materials & Interfaces</i> , 2015 , 7, 690-5	9.5	13
167	Identification of Degradation Mechanisms Based on Thermal Characteristics of InGaN/GaN Laser Diodes. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2015 , 21, 165-170	3.8	4
166	Utilization of polarization-inverted AlInGaN or relatively thinner AlGaIn electron blocking layer in InGaN-based blue-violet laser diodes. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015 , 33, 011209	1.3	7
165	Effect of localization states on the electroluminescence spectral width of blue-green light emitting InGaN/GaN multiple quantum wells. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015 , 33, 061502	2.9	13
164	Beyond spatial correlation effect in micro-Raman light scattering: An example of zinc-blende GaN/GaAs hetero-interface. <i>Journal of Applied Physics</i> , 2015 , 118, 073101	2.5	6
163	Detection of a superconducting phase in a two-atom layer of hexagonal Ga film grown on semiconducting GaN(0001). <i>Physical Review Letters</i> , 2015 , 114, 107003	7.4	64

162	Photoluminescence and Raman mapping characterization of WS ₂ monolayers prepared using top-down and bottom-up methods. <i>Journal of Materials Chemistry C</i> , 2015 , 3, 2589-2592	7.1	33
161	Characteristics of InGaN-based superluminescent diodes with one-sided oblique cavity facet. <i>Science Bulletin</i> , 2014 , 59, 1903-1906		4
160	Polarized and non-polarized photoluminescence of GaInP ₂ alloy with partial CuPt-type atomic ordering: ordered domains vs. disordered regions. <i>Journal of Materials Chemistry C</i> , 2014 , 2, 6119-6124	7.1	11
159	Super transverse diffusion of minority carriers in GaIn _{1-x} P/GaAs double-junction tandem solar cells. <i>Solar Energy</i> , 2014 , 110, 214-220	6.8	5
158	Indoor hospital communication systems: An integrated solution based on power line and visible light communication 2014 ,		22
157	Effects of Fe doping on the strain and optical properties of GaN epilayers grown on sapphire substrates. <i>RSC Advances</i> , 2014 , 4, 55430-55434	3.7	9
156	Unintentionally doped semi-insulating GaN with a low dislocation density grown by metalorganic chemical vapor deposition. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014 , 32, 051207	1.3	13
155	Performance comparison of front- and back-illuminated modes of the AlGaIn-based p-i-n solar-blind ultraviolet photodetectors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014 , 32, 031204	1.3	7
154	Nature of red luminescence band in research-grade ZnO single crystals: A self-activated configurational transition. <i>Applied Physics Letters</i> , 2014 , 105, 041912	3.4	19
153	Two-electron-satellite transition of donor bound exciton in ZnO: Radiative Auger effect. <i>Applied Physics Letters</i> , 2013 , 102, 181909	3.4	11
152	Bias-voltage dependent ultraviolet photodetectors prepared by GaOx+ZnO mixture phase nanocrystalline thin films. <i>Journal of Alloys and Compounds</i> , 2013 , 566, 201-205	5.7	8
151	The effect of Ga-doped nanocrystalline ZnO electrode on deep-ultraviolet enhanced GaN photodetector. <i>Applied Physics Letters</i> , 2013 , 102, 212104	3.4	12
150	Substrate effects on quasiparticles and excitons in graphene nanoflakes. <i>Applied Physics Letters</i> , 2013 , 103, 143109	3.4	20
149	Radiative recombination of carriers in the GaIn _{1-x} P/GaAs double-junction tandem solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2013 , 111, 102-106	6.4	11
148	Performance Enhancement of GaN-Based Laser Diodes With Prestrained Growth. <i>IEEE Photonics Technology Letters</i> , 2013 , 25, 2401-2404	2.2	
147	Influence of aspect ratio on tumbling plates. <i>Journal of Fluid Mechanics</i> , 2013 , 733, 650-679	3.7	12
146	Carbon-coated CdS petalous nanostructures with enhanced photostability and photocatalytic activity. <i>Angewandte Chemie - International Edition</i> , 2013 , 52, 5636-9	16.4	310
145	Optical signature of symmetry variations and spin-valley coupling in atomically thin tungsten dichalcogenides. <i>Scientific Reports</i> , 2013 , 3, 1608	4.9	659

144	Carbon-Coated CdS Petalous Nanostructures with Enhanced Photostability and Photocatalytic Activity. <i>Angewandte Chemie</i> , 2013 , 125, 5746-5749	3.6	106
143	Innentitelbild: Carbon-Coated CdS Petalous Nanostructures with Enhanced Photostability and Photocatalytic Activity (Angew. Chem. 21/2013). <i>Angewandte Chemie</i> , 2013 , 125, 5520-5520	3.6	3
142	Electric field driven magnetic phase transition in graphene nanoflakes. <i>Applied Physics Letters</i> , 2013 , 103, 133103	3.4	17
141	Design Considerations for GaN-Based Blue Laser Diodes With InGaN Upper Waveguide Layer. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2013 , 19, 1500705-1500705	3.8	14
140	Effects of annealing temperature on the characteristics of Ga-doped ZnO film metal-semiconductor-metal ultraviolet photodetectors. <i>Journal of Applied Physics</i> , 2013 , 113, 084501	2.5	19
139	Can interference patterns in the reflectance spectra of GaN epilayers give important information of carrier concentration?. <i>Applied Physics Letters</i> , 2012 , 101, 191102	3.4	8
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